



June 2014

# FDA18N50

## N-Channel UniFET™ MOSFET

### 500 V, 19 A, 265 mΩ

#### Features

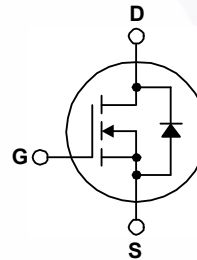
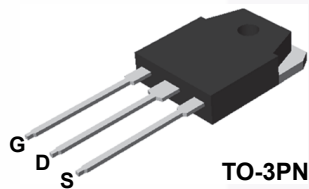
- $R_{DS(on)} = 265 \text{ m}\Omega$  (Max.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 9.5 \text{ A}$
- Low Gate Charge (Typ. 45 nC)
- Low  $C_{rss}$  (Typ. 25 pF)
- 100% Avalanche Tested

#### Applications

- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

#### Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



#### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FDA18N50	Unit
$V_{DSS}$	Drain-Source Voltage	500	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	19
		- Continuous ( $T_C = 100^\circ\text{C}$ )	11.4
$I_{DM}$	Drain Current	- Pulsed (Note 1)	76
$V_{GSS}$	Gate-Source voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	945	mJ
$I_{AR}$	Avalanche Current (Note 1)	19	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	23	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	239
		- Derate above $25^\circ\text{C}$	1.92
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

#### Thermal Characteristics

Symbol	Parameter	FDA18N50	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.52	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	

FDA18N50 — N-Channel UniFET™ MOSFET

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDA18N50	FDA18N50	TO-3PN	Tube	N/A	30 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

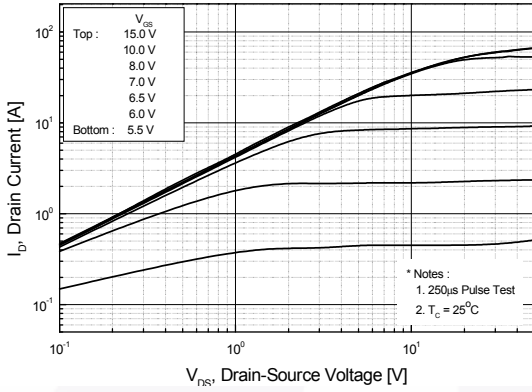
Symbol	Parameter	Conditions	Min.	Typ.	Max	Unit
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	500	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$ , Referenced to $25^\circ\text{C}$	--	0.5	--	$V/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 500V, V_{GS} = 0V$ $V_{DS} = 400V, T_C = 125^\circ\text{C}$	--	--	1 10	$\mu A$ $\mu A$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30V, V_{DS} = 0V$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30V, V_{DS} = 0V$	--	--	-100	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 9.5A$	--	0.220	0.265	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 40V, I_D = 9.5A$	--	25	--	S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0\text{MHz}$	--	2200	2860	pF
$C_{oss}$	Output Capacitance		--	330	430	pF
$C_{rss}$	Reverse Transfer Capacitance		--	25	40	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250V, I_D = 19A$ $R_G = 25\Omega$	--	55	120	ns
$t_r$	Turn-On Rise Time		--	165	340	ns
$t_{d(off)}$	Turn-Off Delay Time		--	95	200	ns
$t_f$	Turn-Off Fall Time		(Note 4)	--	90	190
$Q_g$	Total Gate Charge	$V_{DS} = 400V, I_D = 19A$ $V_{GS} = 10V$	--	45	60	nC
$Q_{gs}$	Gate-Source Charge		--	12.5	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4)	--	19	--
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current		--	--	19	A
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current		--	--	76	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_S = 19A$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0V, I_S = 19A$ $di_F/dt = 100A/\mu s$	--	500	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	5.4	--	$\mu C$

### NOTES:

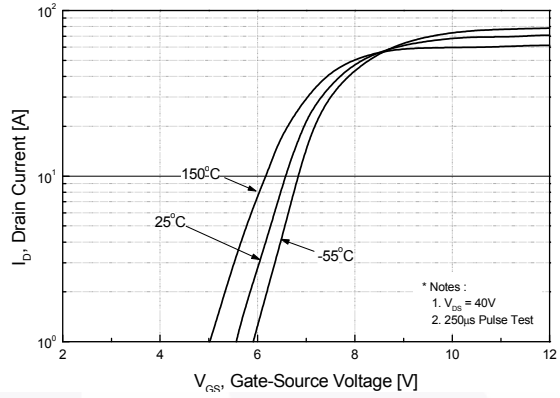
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L = 4.7\text{mH}, I_{AS} = 19A, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 19A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Essentially Independent of Operating Temperature Typical Characteristics

## Typical Characteristics

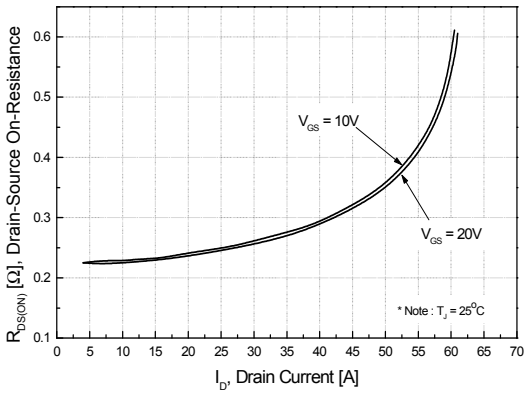
**Figure 1. On-Region Characteristics**



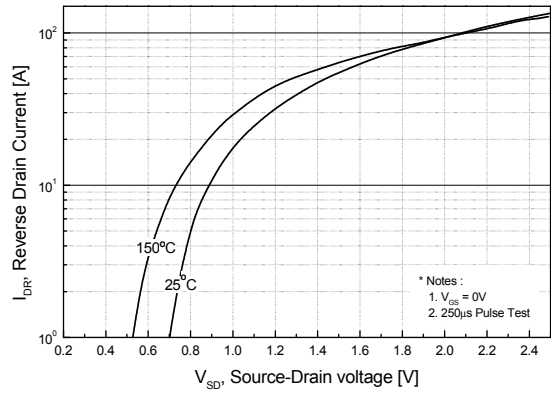
**Figure 2. Transfer Characteristics**



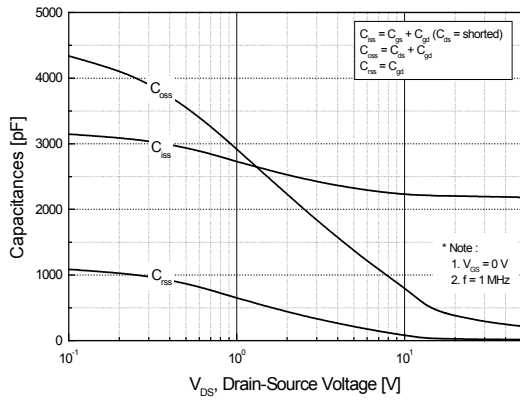
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



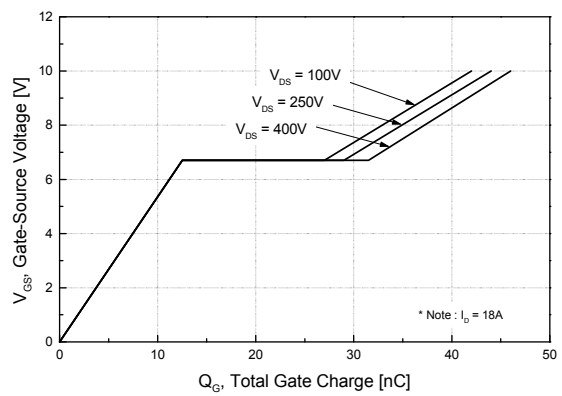
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**



**Figure 6. Gate Charge Characteristics**



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

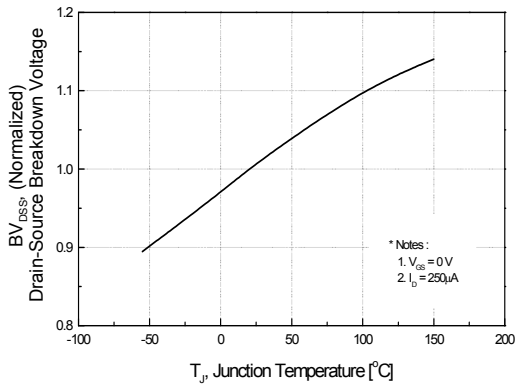


Figure 8. On-Resistance Variation vs. Temperature

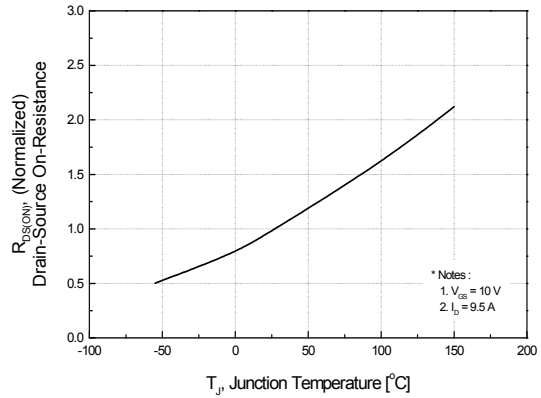


Figure 9. Maximum Safe Operating Area

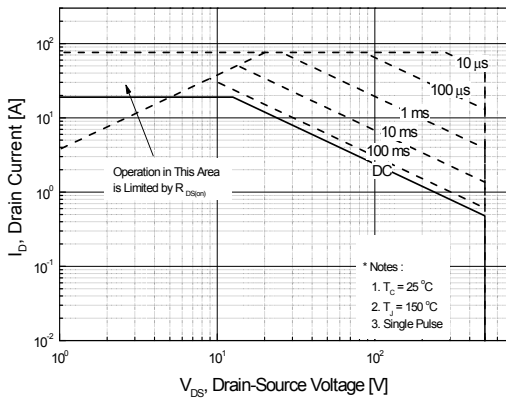


Figure 10. Maximum Drain Current vs. Case Temperature

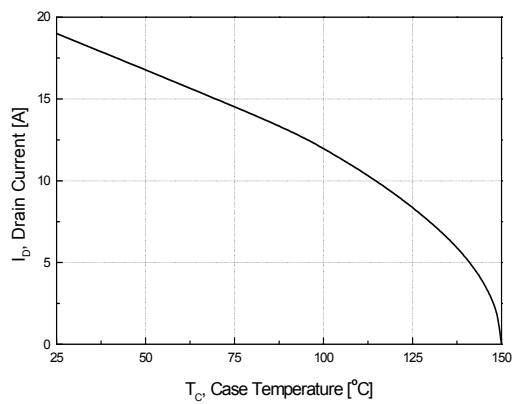


Figure 11. Transient Thermal Response Curve

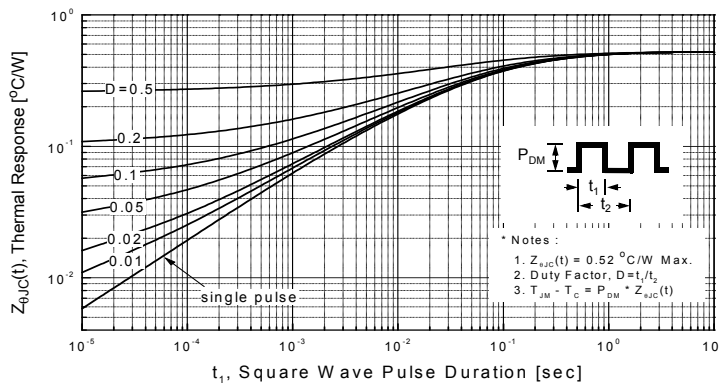


Figure 12. Gate Charge Test Circuit & Waveform

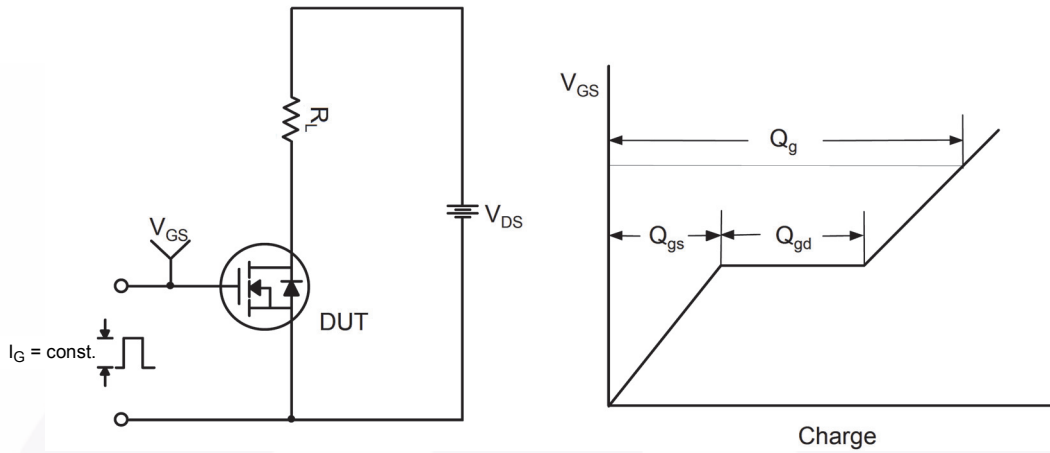


Figure 13. Resistive Switching Test Circuit & Waveforms

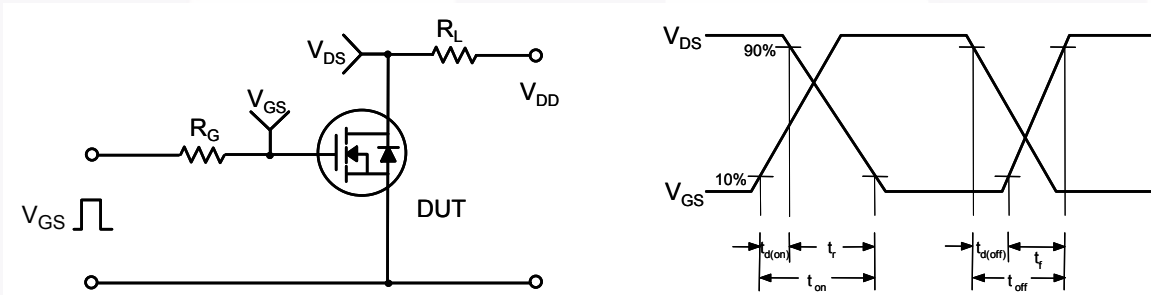


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

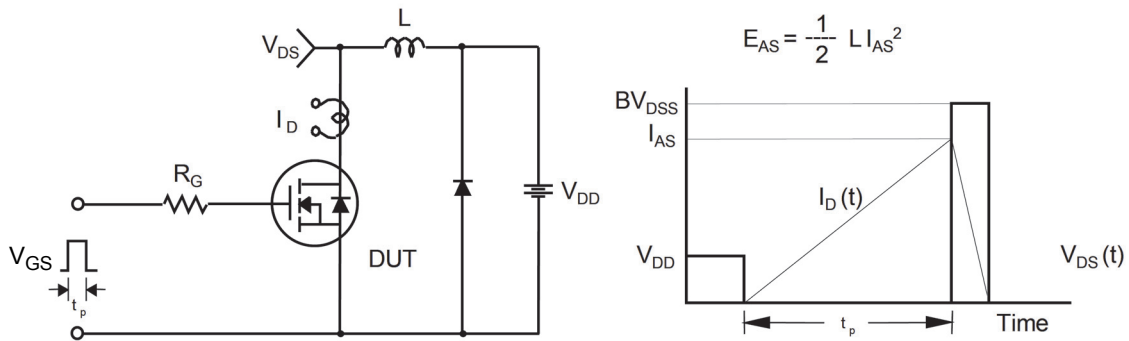
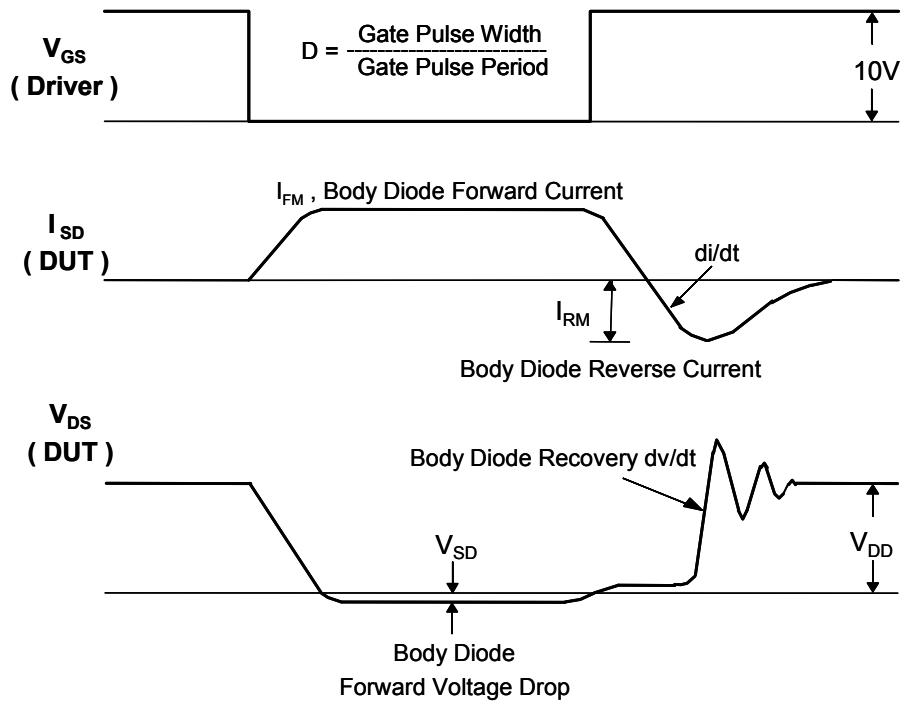
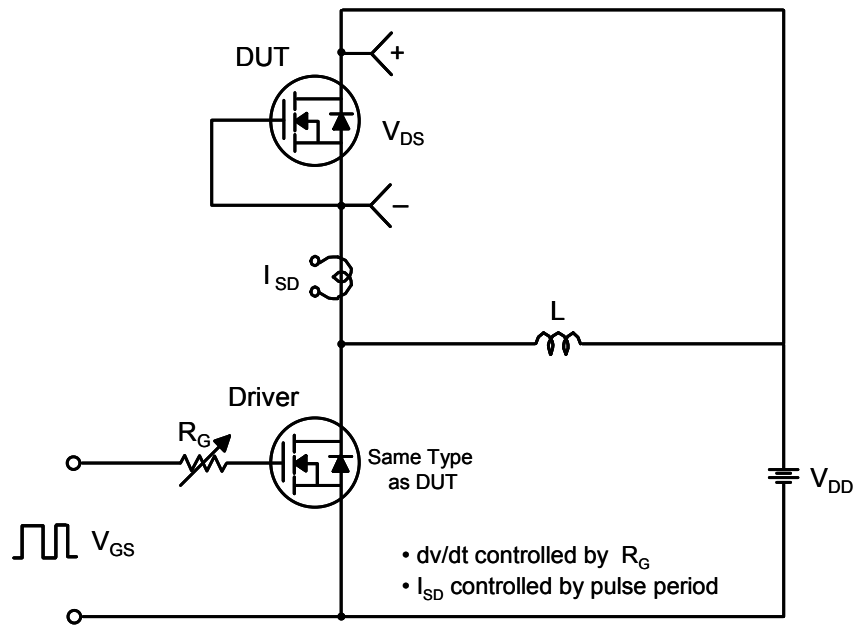
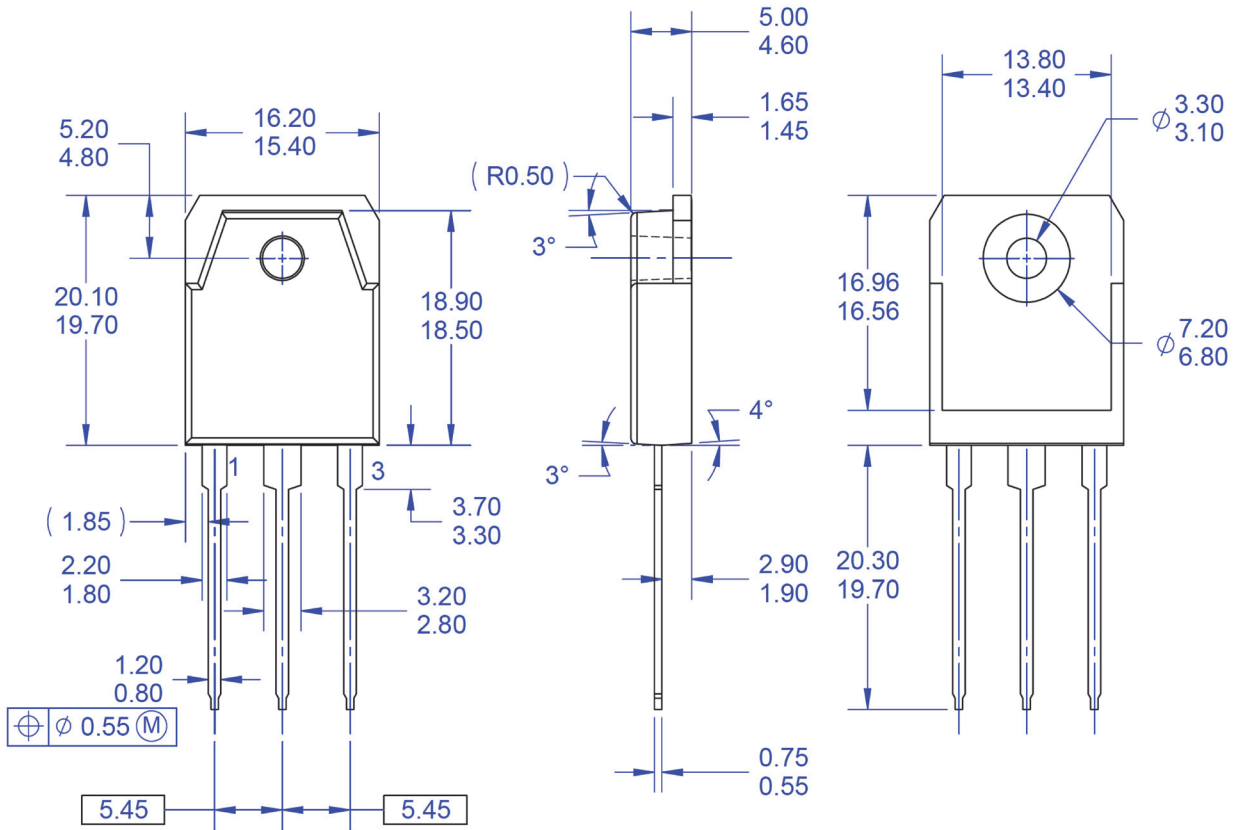


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

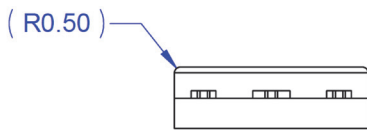


**Mechanical Dimensions**



NOTES: UNLESS OTHERWISE SPECIFIED

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- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- E) DRAWING FILE NAME: TO3PN03AREV1.
- F) FAIRCHILD SEMICONDUCTOR.



**Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65**

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